

# FDS4685

## 40V P-Channel PowerTrench® MOSFET

### Features

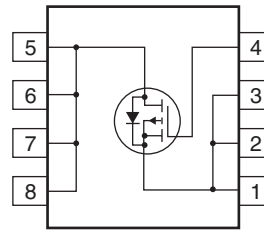
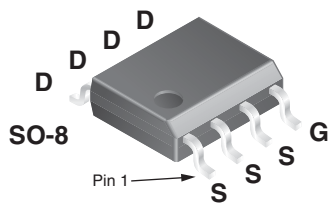
- -8.2 A, -40 V  $R_{DS(ON)} = 0.027 \Omega @ V_{GS} = -10 \text{ V}$   
 $R_{DS(ON)} = 0.035 \Omega @ V_{GS} = -4.5 \text{ V}$
- Fast switching speed
- High performance trench technology for extremely low  $R_{DS(ON)}$
- High power and current handling capability

### Applications

- Power management
- Load switch
- Battery protection

### General Description

This P-Channel MOSFET is a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications requiring a wide range of gate drive voltage ratings (4.5V – 20V).



### Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	-40	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current - Continuous (Note 1a) - Pulsed	-8.2	A
		-50	
$P_D$	Power Dissipation for Single Operation (Note 1a) (Note 1b) (Note 1c)	2.5	W
		1.4	
		1.2	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$
<b>Thermal Characteristics</b>			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1c)	125	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	

### Package Marking and Ordering Information

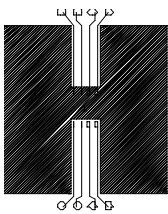
Device Marking	Device	Reel Size	Tape width	Quantity
FDS4685	FDS4685	13"	12mm	2500 units

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise noted

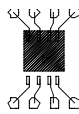
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-40			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-32		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -32\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			$\pm 100$	nA
<b>On Characteristics (Note 2)</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-1	-1.6	-3	V
$\Delta V_{GS(th)} / \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		4.7		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -8.2\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -7\text{ A}$ $V_{GS} = -10\text{ V}, I_D = -8.2\text{ A}, T_J = 125^\circ\text{C}$		22 29 31	27 35 42	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -8.2\text{ A}$		22		S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		1872		pF
$C_{oss}$	Output Capacitance			256		pF
$C_{rss}$	Reverse Transfer Capacitance			134		pF
$R_G$	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1\text{ MHz}$		4		$\Omega$
<b>Switching Characteristics (Note 2)</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -20\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -10\text{ V}, R_{GEN} = 6\ \Omega$		14	25	ns
$t_r$	Turn-On Rise Time			11	20	ns
$t_{d(off)}$	Turn-Off Delay Time			50	80	ns
$t_f$	Turn-Off Fall Time			18	32	ns
$Q_g$	Total Gate Charge	$V_{DS} = -20\text{ V}, I_D = -8.2\text{ A},$ $V_{GS} = -5\text{ V}$		19	27	nC
$Q_{gs}$	Gate-Source Charge			5.6		nC
$Q_{gd}$	Gate-Drain Charge			6.1		nC
<b>Drain-Source Diode Characteristics</b>						
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -2.1\text{ A}$ (Note 2)		-0.7	-1.2	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = -8.2\text{ A},$ $d_i I_F / d_t = 100\text{ A}/\mu\text{s}$		26		nS
$Q_{rr}$	Diode Reverse Recovery Charge			15		nC

**Notes:**

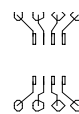
- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $50^\circ\text{C}/\text{W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper



b)  $105^\circ\text{C}/\text{W}$  when mounted on a  $.04\text{ in}^2$  pad of 2 oz copper

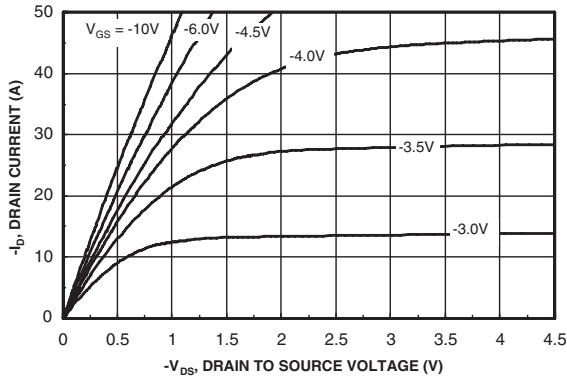


c)  $125^\circ\text{C}/\text{W}$  when mounted on a minimum pad.

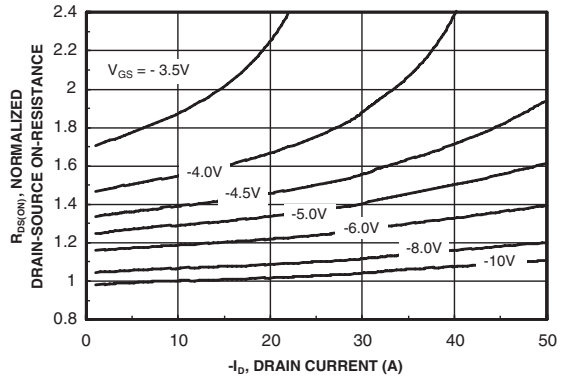
Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width <  $300\ \mu\text{s}$ , Duty Cycle < 2.0%

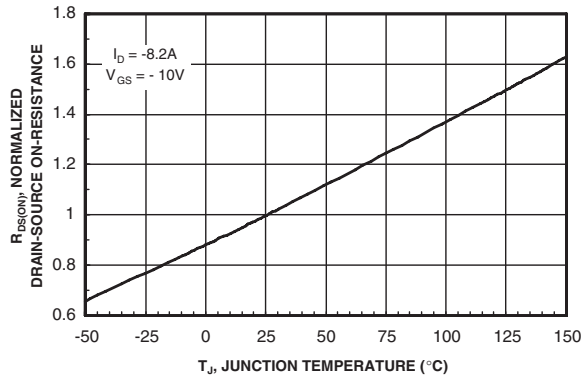
**Typical Characteristics:**



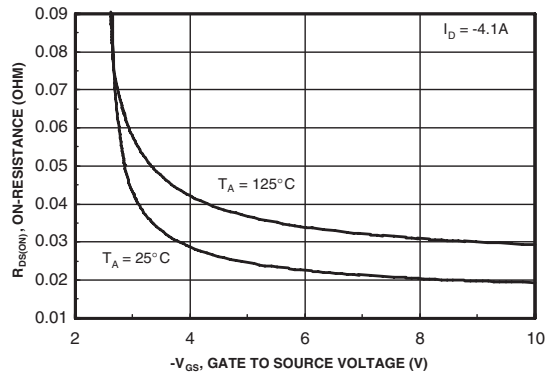
**Figure 1. On-Region Characteristics.**



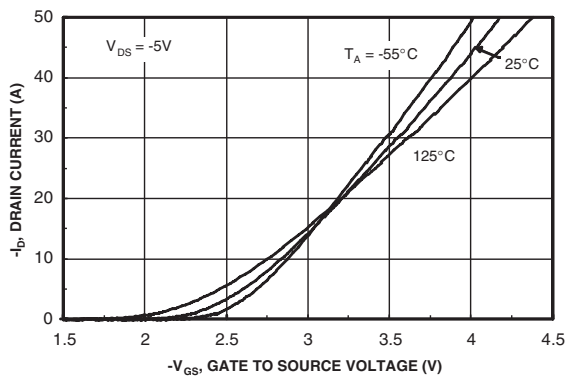
**Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.**



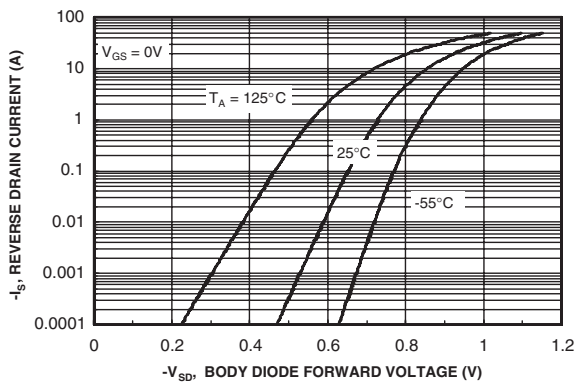
**Figure 3. On-Resistance Variation with Temperature.**



**Figure 4. On-Resistance Variation with Gate-to-Source Voltage.**

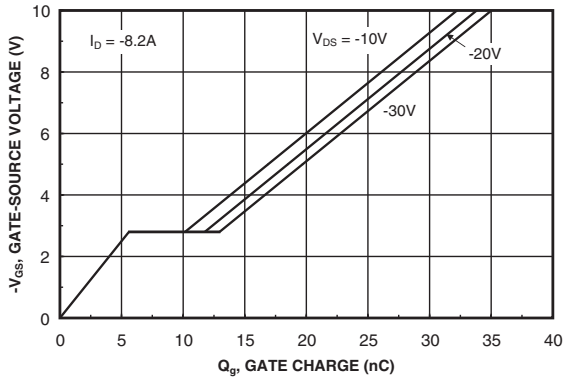


**Figure 5. Transfer Characteristics.**

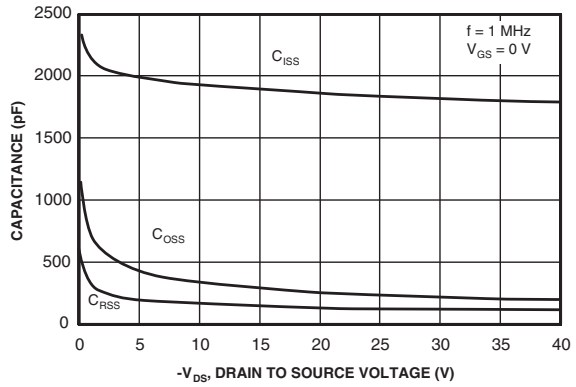


**Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.**

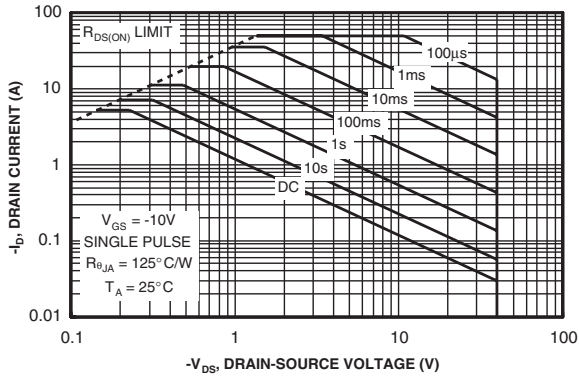
**Typical Characteristics:**



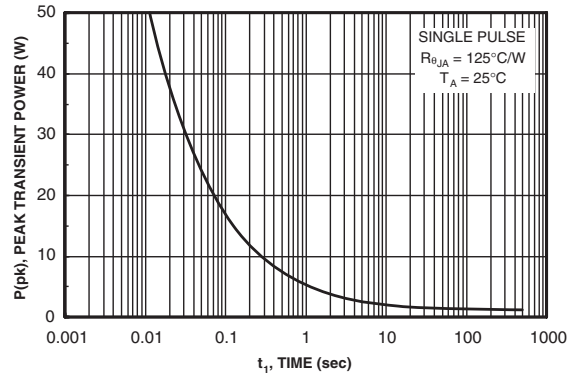
**Figure 7. Gate Charge Characteristics.**



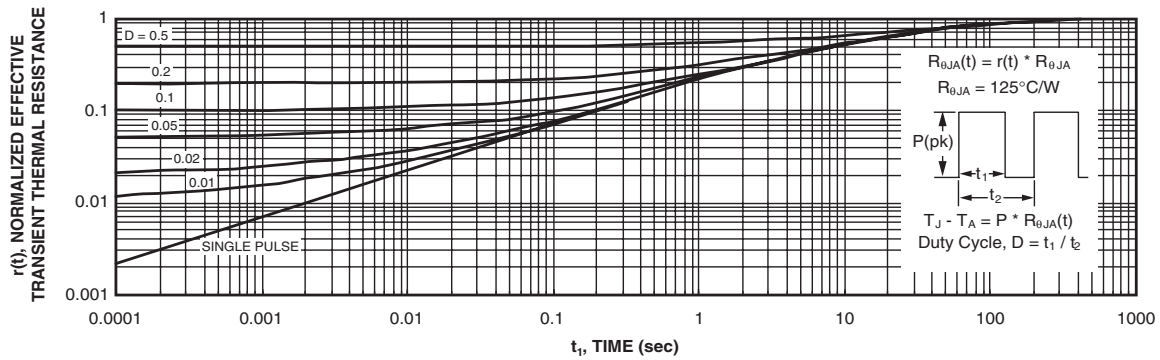
**Figure 8. Capacitance Characteristics.**



**Figure 9. Maximum Safe Operating Area.**



**Figure 10. Single Pulse Maximum Power Dissipation.**



**Figure 11. Transient Thermal Response Curve.**

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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FACT Quiet Series™		OCXPro™	RapidConnect™	UHC™
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